

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	12681	electrode with concentration with impurit\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/26 20:10
S2	3552	electrode with concentration adj impurit\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/01/06 18:50
S3	1729	electrode with concentration adj impurit\$3 and gate adj insulat\$4 with film	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/01/06 18:51
S4	980	electrode with concentration adj impurit\$3 and gate adj insulat\$4 with film with thick\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/01/06 18:52
S5	928	electrode with concentration adj impurit\$3 and gate adj insulat\$4 with film with thick\$4 and transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/01/06 18:52
S6	16	electrode near concentration adj impurit\$3 and gate adj insulat\$4 with film with thick\$4 and transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/01/06 19:30
S7	17	electrode near concentration near impurit\$3 and gate adj insulat\$4 with film with thick\$4 and transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/20 10:22
S8	1010	(438/275).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/20 10:20

## EAST Search History

S9	0	("008and7").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/06 19:34
S10	0	S8 and S7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/01/06 19:35
S11	10	S8 and S5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/01/06 19:52
S12	659	257/392	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/10/20 10:20
S13	15	S12 and S3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/10/20 10:21
S14	118382	polysilicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/01/07 18:21
S15	0	dpoing with gate adj electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/01/07 18:24
S16	7938	doping with polysilicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 18:34

## EAST Search History

S17	157231	gate adj electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 18:32
S18	709	S16 with S17	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/20 10:21
S19	34	S16 with S17 same known	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/09 07:21
S20	919	doping with concentration with polysilicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 18:37
S21	1	S20 with S17 with known	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 18:35
S22	3	S20 same S17 with known	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 18:35
S23	9	doping with concentration with polysilicon with known	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 18:37
S24	71	effective with insulation adj layer with thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/09 07:22

## EAST Search History

S25	6	effective with insulation adj layer with thickness same gate adj electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/15 11:04
S26	1485	(257/288).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/20 10:21
S27	392	(257/402).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/09 08:10
S28	243	(257/407).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/09 08:10
S29	2	("6507073").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/09 22:12
S30	6	effective with insulation adj layer with thickness same gate adj electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/15 11:33
S31	367	effective with layer with thickness same gate adj electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/15 11:33
S32	1297207	effective with layer with thickness same gate adj electrode and dop\$3 concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/15 11:33

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S33	59	effective with layer with thickness same gate adj electrode and dop\$3 concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/06/15 11:34
S34	9	effective with layer with thickness same gate adj electrode same dop\$3 concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/06/15 16:21
S35	2	("20020072182").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/15 12:23
S36	9	effective with layer with thickness same gate adj electrode with dop\$3 concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/06/15 16:33
S37	13	effective with thickness same gate adj electrode with dop\$3 concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/06/15 16:27
S38	17	effective with thickness same gate adj electrode with impurity concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/06/15 16:33
S39	20	effective with thickness same gate adj electrode with impurity near concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/06/15 16:33
S40	275	effective with thickness and gate adj electrode with impurity near concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/06/15 16:32

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S41	348	effective with thickness and gate adj electrode with impurity near concentration and transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/15 16:33
S42	9	effective with layer with thickness same gate adj electrode with dop\$3 concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/15 16:33
S43	22	effective with thickness same gate adj electrode with impurity near concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/26 17:18
S44	18	effective with thickness same gate adj electrode with impurity concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/15 16:33
S45	2	("6660598").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/19 15:12
S46	29	effective with thickness same electrode with impurity near concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/26 17:20
S47	148	effective with thickness same electrode with concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/26 17:19
S48	22	effective with thickness same gate with electrode same doping with concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/27 11:44

## EAST Search History

S49	21622	shadow mask	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/26 20:10
S50	956	shadow mask and oled	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/27 09:30
S51	21	plasma ion implantation system	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/27 10:11
S52	1675	different with gate oxide with thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/27 10:12
S53	41	different transistor with gate oxide with thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/20 10:24
S54	2	("5468666").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/27 10:45
S55	1567	(257/288).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/27 11:44
S56	401	(257/402).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/20 10:21

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S57	262	(257/407).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/20 10:21
S58	1109	(438/275).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/20 10:20
S59	740	257/392	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/10/20 10:20
S60	1991	electrode with concentration adj impurit\$3 and gate adj insulat\$4 with film	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/20 10:21
S61	740	257/392	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/10/20 10:21
S62	23	S61 and S60	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/10/20 10:21
S63	8627	doping with polysilicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/20 10:21
S64	170632	gate adj electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/20 10:21



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S65	774	S63 with S64	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/20 10:21
S66	1656	(257/288).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/20 10:21
S67	409	(257/402).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/20 10:21
S68	274	(257/407).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/20 10:21
S69	21	electrode near concentration near impurit\$3 and gate adj insulat\$4 with film with thick\$4 and transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/20 10:22
S70	43	different transistor with gate oxide with thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/20 11:12
S71	42	(257/e29.111).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/20 11:14
S73	2	OHGISHI-YUKO.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/20 11:15